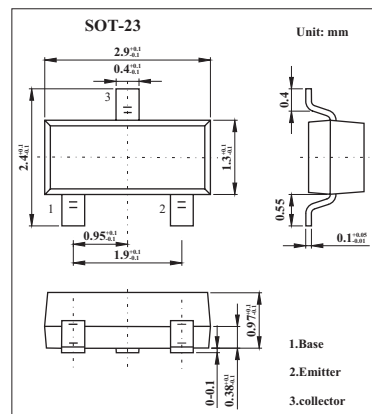


2SA811A

■ Features

- High DC current gain.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-120	V
Collector-emitter voltage	V _{CEO}	-120	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current	I _C	-50	mA
Total power dissipation	P _T	200	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = -120V, I _E =0			-50	nA
Emitter cutoff current	I _{EB0}	V _{EB} = -5V, I _C =0			-50	nA
DC current gain *	h _{FE}	V _{CE} = -6V, I _C = -1mA	135	500	900	
		V _{CE} = -6V, I _C = -0.1mA	100	500		
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C = -10mA, I _B = -1mA		-0.09	-0.30	V
Base-emitter voltage *	V _{BE}	V _{CE} = -6V, I _C = -1mA	-0.55	-0.61	-0.65	V
Gain bandwidth product	f _T	V _{CE} = -6V, I _E = 1mA	50	90		MHz
Output capacitance	C _{ob}	V _{CB} = -30V, I _E = 0, f = 1.0MHz		2.0	3.0	pF

* Pulse test: t_p ≤ 350 μs; d ≤ 0.02.

■ hFE Classification

Marking	C15	C16	C17	C18
hFE	135~270	200~400	300~600	450~900